Title (en)

APPLICATIONS OF NANO-ENABLED LARGE AREA MACROELECTRONIC SUBSTRATES INCORPORATING NANOWIRES AND NANOWIRE COMPOSITES

Title (de)

ANWENDUNG VON NANO-BEREITEN GROSSFLûCHIGEN MAKROELEKTRONISCHEN SUBSTRATEN MIT NANOLEITUNGEN UND NANOLEITUNGSZUSAMMENSETZUNGEN

Title (fr)

APPLICATIONS DE SUBSTRATS MACRO-ELECTRONIQUES DE GRANDE SURFACE NANO-ACTIVES INCORPORANT DES NANOFILS ET DES COMPOSITES DE NANOFIL

Publication

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Application

EP 03799305 A 20030930

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Abstract (en)

[origin: WO2004032191A2] Macroelectronic substrate materials incorporating nanowires are described. These are used to provide underlying electronic elements (e.g., transistors and the like) for a variety of different applications. Methods for making the macroelectronic substrate materials are disclosed. One application is for transmission an reception of RF signals in small, lightweight sensors. Such sensors can be configured in a distributed sensor network to provide security monitoring. Furthermore, a method and apparatus for a radio frequency identification (RFID) tag is described. The RFID tag includes an antenna and a beam-steering array. The beam-steering array includes a plurality of tunable elements. A method and apparatus for an acoustic cancellation device and for an adjustable phase shifter that are enabled by nanowires are also described.

IPC 1-7

C01B 31/02; H03H 11/20; H01L 29/06; H01L 21/00

IPC 8 full level

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